

wherein said first gate electrode partially overlaps said pair of LDD regions,
and

said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with
a second gate insulating film interposed therebetween, said second semiconductor layer comprising
a second channel formation region and second source and drain regions being in contact with said
second channel formation region,

wherein said second gate electrode partially overlaps said second source and drain
regions, and

wherein a wiring is connected to at least one of said second source and drain regions.

Cancel Claim 13.

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24. (Fourth Amendment) A goggle type display device having an n-channel TFT and a p-
channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode formed adjacent to a first semiconductor layer with a first
gate insulating film interposed therebetween, said first semiconductor layer comprising a first
channel formation region, a pair of LDD regions and first source and drain regions;

wherein said first gate electrode partially overlaps said pair of LDD regions,
and

said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with